

Q1 metal electrode; plate electrodes; and interlevel dielectric film. The semiconductor region is defined in the substrate. The drain region is defined approximately at the center of the semiconductor region. The body region is defined in the semiconductor region so as to be spaced apart from, and to surround, the drain region. The source region is defined in the body region. The gate insulating film is deposited over the body region. The gate electrode is formed on the gate insulating film. The field insulating film is deposited over a part of the semiconductor region between the body and drain regions. The metal electrode is electrically connected to the drain region. The plate electrodes are in an electrically floating plate state, and are spaced apart from, and surround, the drain region when the device is viewed from over the substrate. And the interlevel dielectric film is formed over the gate insulating film, the field insulating film and the plate electrodes. This device is characterized in that parts of the metal electrode are extended onto the interlevel dielectric film and located over the respective plate electrodes and that each said part of the metal electrode is capacitively coupled to an associated one of the plate electrodes.

In the Claims:

Please amend claim 1 as follows:

1. (Amended) A semiconductor device with a high breakdown voltage, comprising :

- Q2
- a semiconductor substrate of a first conductivity type;
 - a semiconductor region of a second conductivity type, which is defined in the substrate;
 - a drain region of the second conductivity type, which is defined approximately at the center of the semiconductor region;
 - a body region of the first conductivity type, which is defined in the semiconductor